μA747

DUAL FREQUENCY COMPENSATED OPERATIONAL AMPLIFIER

FAIRCHILD LINEAR INTEGRATED CIRCUITS

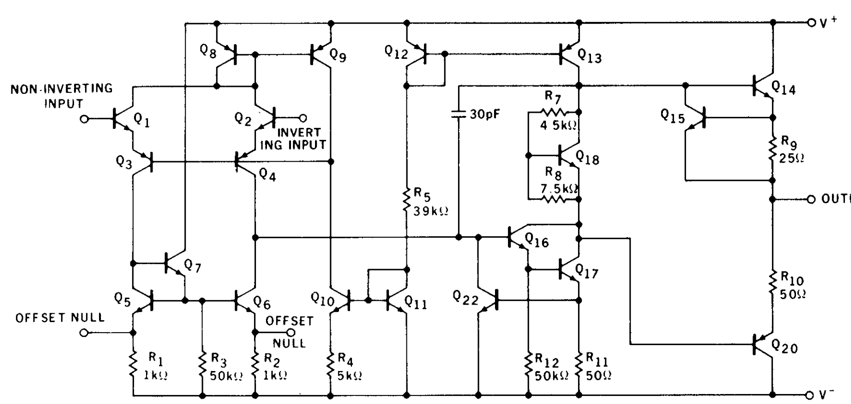
GENERAL DESCRIPTION – The μA747 is a pair of high performance monolithic operational amplifiers constructed on a single silicon chip, using the Fairchild Planar* epitaxial process. They are intended for a wide range of analog applications where board space or weight are important. High common mode voltage range and absence of "latch-up" make the μA747 ideal for use as a voltage follower. The high gain and wide range of operating voltage provides superior performance in integrator, summing amplifier, and general feedback applications. The μA747 is short-circuit protected and requires no external components for frequency compensation. The internal 6 dB/octave roll-off insures stability in closed loop applications. For single amplifier performance, see μA741 data sheet.

- **NO FREQUENCY COMPENSATION REQUIRED**
- **SHORT-CIRCUIT PROTECTION**
- **OFFSET VOLTAGE NULL CAPABILITY**
- **LARGE COMMON-MODE AND DIFFERENTIAL VOLTAGE RANGES**
- **LOW POWER CONSUMPTION**
- **NO LATCH UP**

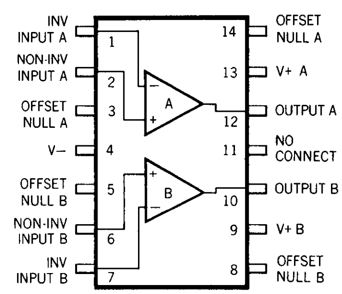
ABSOLUTE MAXIMUM RATINGS

Supply Voltage	
Military (312 Grade)	±22 V
Commercial (393 Grade)	±18 V
Internal Power Dissipation (Note 1)	
Metal Can	500 mW
Ceramic DIP	670 mW
Differential Input Voltage	±30 V
Input Voltage (Note 2)	±15 V
Voltage between Offset Null and V−	±0.5 V
Storage Temperature Range	−65°C to +150°C
Operating Temperature Range	−55°C to +125°C
Lead Temperature (Soldering, 60 seconds)	300°C
Output Short-Circuit Duration (Note 3)	Indefinite

EQUIVALENT CIRCUIT (Each Side)

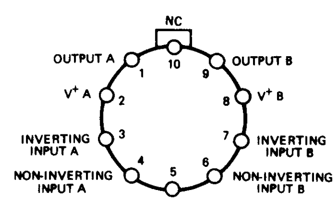


CONNECTION DIAGRAMS
(TOP VIEWS)
14 LEAD DIP



ORDER PART NOS.
U7A7747312
U7A7747393

10 LEAD METAL CAN



ORDER PART NOS.
U5F7747312
U5F7747393

Notes on following pages.

*Planar is a patented Fairchild process.

312 GRADE

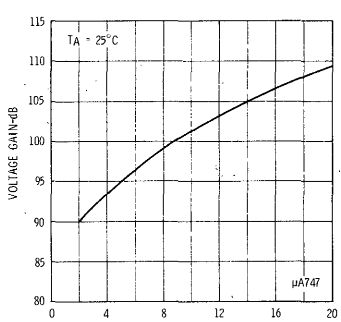
ELECTRICAL CHARACTERISTICS — Each Amplifier ($V_S = \pm15$ V, $T_A = 25°C$ unless otherwise specified)

PARAMETERS (see definitions)	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Input Offset Voltage	$R_S \leq 10$ kΩ		1.0	5.0	mV
Input Offset Current			20	200	nA
Input Bias Current			80	500	nA
Input Resistance		0.3	2.0		MΩ
Input Capacitance			1.4		pF
Offset Voltage Adjustment Range			±15		mV
Large-Signal Voltage Gain	$R_L \geq 2$ kΩ, $V_{out} = \pm10$ V	50,000	200,000		
Output Resistance			75		Ω
Output Short-Circuit Current			25		mA
Supply Current			1.7	2.8	mA
Power Consumption			50	85	mW
Transient Response (unity gain)	$V_{in} = 20$ mV, $R_L = 2$ kΩ, $C_L \leq 100$ pF				
Risetime			0.3		μs
Overshoot			5.0		%
Slew Rate	$R_L \geq 2$ kΩ		0.5		V/μs
Channel Separation			120		dB
The following specifications apply for $-55°C \leq T_A \leq +125°C$.					
Input Offset Voltage	$R_S \leq 10$ kΩ		1.0	6.0	mV
Input Offset Current	$T_A = +125°C$		7.0	200	nA
	$T_A = -55°C$		85	500	nA
Input Bias Current	$T_A = +125°C$		0.03	0.5	μA
	$T_A = -55°C$		0.3	1.5	μA
Input Voltage Range		±12	±13		V
Common Mode Rejection Ratio	$R_S \leq 10$ kΩ	70	90		dB
Supply Voltage Rejection Ratio	$R_S \leq 10$ kΩ		30	150	μV/V
Large-Signal Voltage Gain	$R_L \geq 2$ kΩ, $V_{out} = \pm10$ V	25,000			
Output Voltage Swing	$R_L \geq 10$ kΩ	±12	±14		V
	$R_L \geq 2$ kΩ	±10	±13		V
Supply Current	$T_A = +125°C$		1.5	2.5	mA
	$T_A = -55°C$		2.0	3.3	mA
Power Consumption	$T_A = +125°C$		45	75	mW
	$T_A = -55°C$		60	100	mW

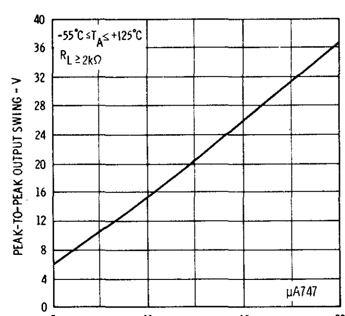
TYPICAL PERFORMANCE CURVES (Each Amplifier)

TYPICAL PERFORMANCE CURVES

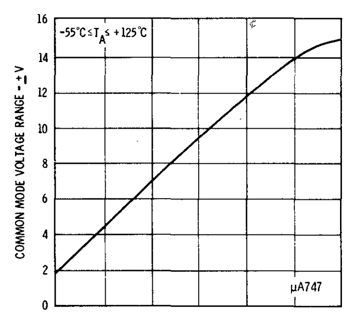
OPEN LOOP VOLTAGE GAIN AS A FUNCTION OF SUPPLY VOLTAGE



OUTPUT VOLTAGE SWING AS A FUNCTION OF SUPPLY VOLTAGE



INPUT COMMON MODE VOLTAGE RANGE AS A FUNCTION OF SUPPLY VOLTAGE



393 GRADE

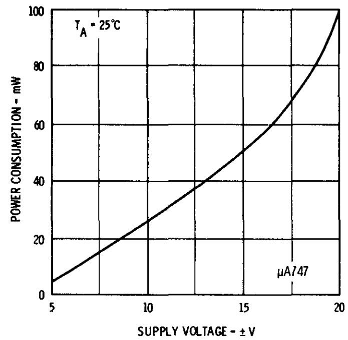
ELECTRICAL CHARACTERISTICS — Each Amplifier ($V_S = \pm15$ V, $T_A = 25°C$ unless otherwise specified)

PARAMETERS (see definitions)	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Input Offset Voltage	$R_S \leq 10$ kΩ		1.0	6.0	mV
Input Offset Current			20	200	nA
Input Bias Current			80	500	nA
Input Resistance		0.3	2.0		MΩ
Input Capacitance			1.4		pF
Offset Voltage Adjustment Range			±15		mV
Large-Signal Voltage Gain	$R_L \geq 2$ kΩ, $V_{out} = \pm10$ V	25,000	200,000		
Output Resistance			75		Ω
Output Short-Circuit Current			25		mA
Supply Current			1.7	2.8	mA
Power Consumption			50	85	mW
Transient Response (unity gain)	$V_{in} = 20$ mV, $R_L = 2$ kΩ, $C_L \leq 100$ pF				
Risetime			0.3		μs
Overshoot			5.0		%
Slew Rate	$R_L \geq 2$ kΩ		0.5		V/μs
Channel Separation			120		dB
The following specifications apply for $0°C \leq T_A \leq +70°C$.					
Input Offset Voltage	$R_S \leq 10$ kΩ		1.0	7.5	mV
Input Offset Current			7.0	300	nA
Input Bias Current			0.03	0.8	μA
Input Voltage Range		±12	±13		V
Common Mode Rejection Ratio	$R_S \leq 10$ kΩ	70	90		dB
Supply Voltage Rejection Ratio	$R_S \leq 10$ kΩ		30	150	μV/V
Large-Signal Voltage Gain	$R_L \geq 2$ kΩ, $V_{out} = \pm10$ V	15,000			
Output Voltage Swing	$R_L \geq 10$ kΩ	±12	±14		V
	$R_L \geq 2$ kΩ	±10	±13		V
Supply Current			2.0	3.3	mA
Power Consumption			60	100	mW

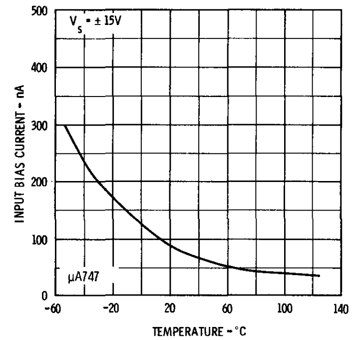
NOTES
1. Rating applies to ambient temperatures up to 70°C. Above 70°C ambient derate linearly at 6.3 mW/°C for the Metal Can and 8.3 mW/°C for the Ceramic DIP package.
2. For supply voltages less than ±15 V, the absolute maximum input voltage is equal to the supply voltage.
3. Short circuit may be to ground or either supply. Military rating applies to +125°C case temperature or +60°C ambient temperature for each side.

TYPICAL PERFORMANCE CURVES (Each Amplifier)

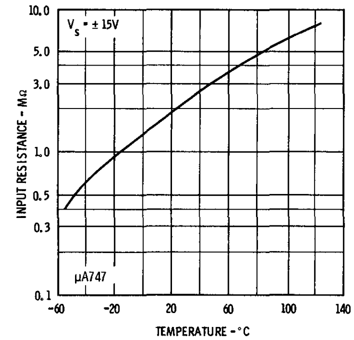
POWER CONSUMPTION AS A FUNCTION OF SUPPLY VOLTAGE



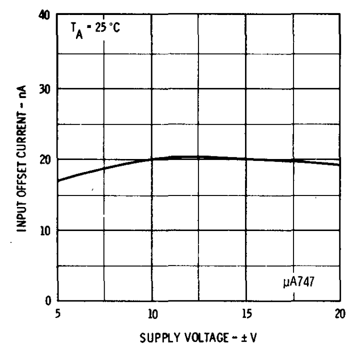
INPUT BIAS CURRENT AS A FUNCTION OF AMBIENT TEMPERATURE



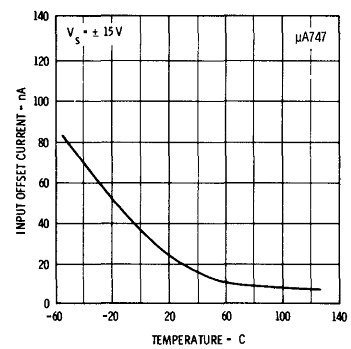
INPUT RESISTANCE AS A FUNCTION OF AMBIENT TEMPERATURE



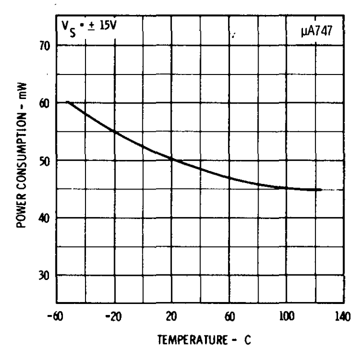
INPUT OFFSET CURRENT AS A FUNCTION OF SUPPLY VOLTAGE



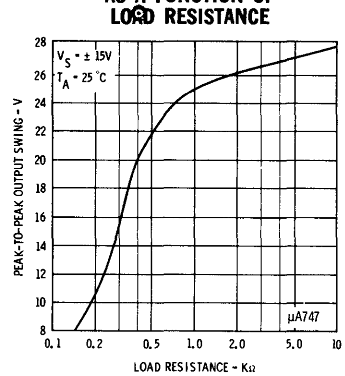
INPUT OFFSET CURRENT AS A FUNCTION OF AMBIENT TEMPERATURE



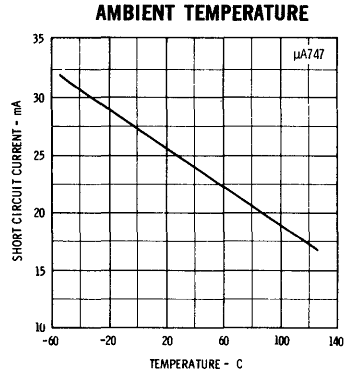
POWER CONSUMPTION AS A FUNCTION OF AMBIENT TEMPERATURE



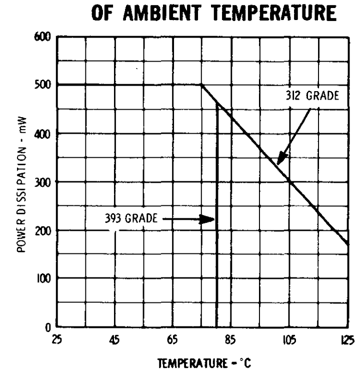
OUTPUT VOLTAGE SWING AS A FUNCTION OF LOAD RESISTANCE



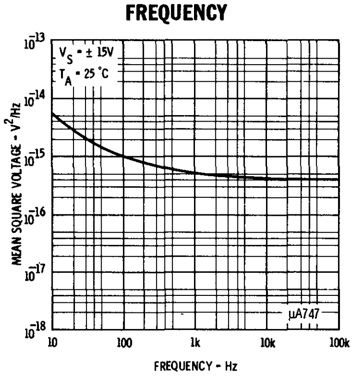
OUTPUT SHORT-CIRCUIT CURRENT AS A FUNCTION OF AMBIENT TEMPERATURE



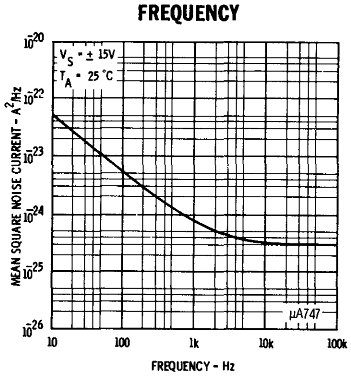
ABSOLUTE MAXIMUM POWER DISSIPATION AS A FUNCTION OF AMBIENT TEMPERATURE



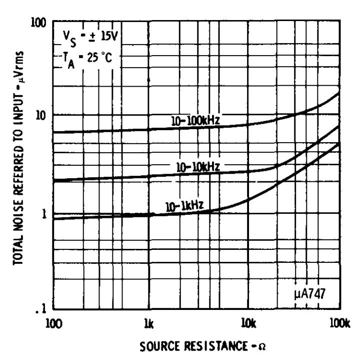
INPUT NOISE VOLTAGE AS A FUNCTION OF FREQUENCY



INPUT NOISE CURRENT AS A FUNCTION OF FREQUENCY

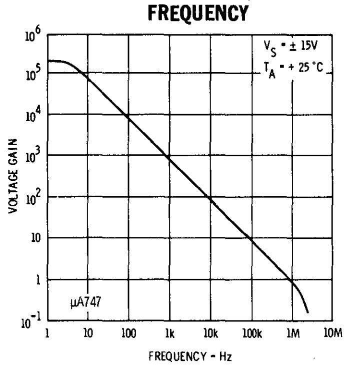


BROADBAND NOISE FOR VARIOUS BANDWIDTHS

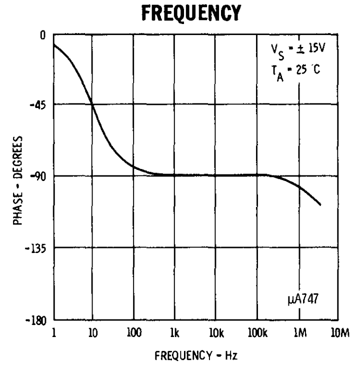


TYPICAL PERFORMANCE CURVES (Each Amplifier)

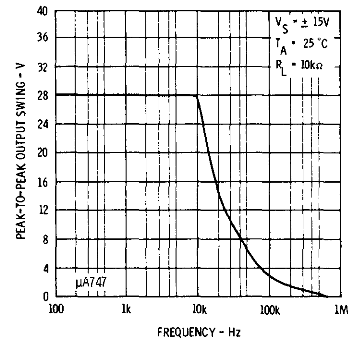
OPEN LOOP VOLTAGE GAIN AS A FUNCTION OF FREQUENCY



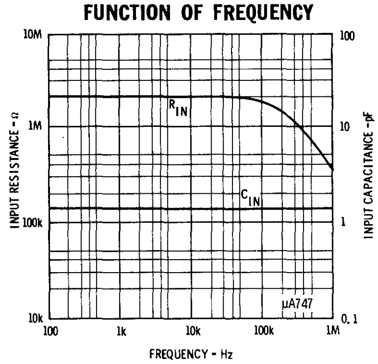
OPEN LOOP PHASE RESPONSE AS A FUNCTION OF FREQUENCY



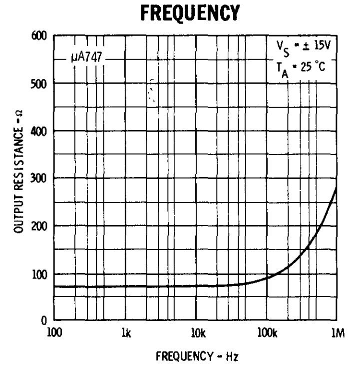
OUTPUT VOLTAGE SWING AS A FUNCTION OF FREQUENCY



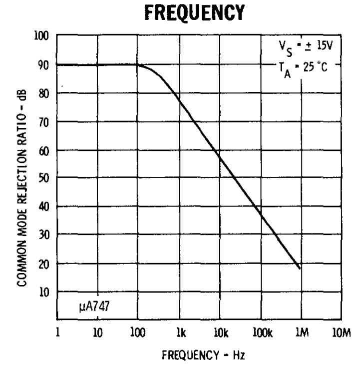
INPUT RESISTANCE AND INPUT CAPACITANCE AS A FUNCTION OF FREQUENCY



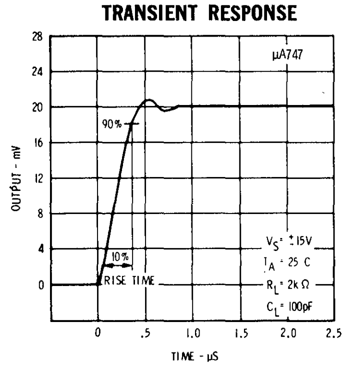
OUTPUT RESISTANCE AS A FUNCTION OF FREQUENCY



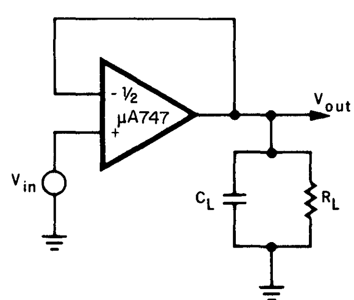
COMMON MODE REJECTION RATIO AS A FUNCTION OF FREQUENCY



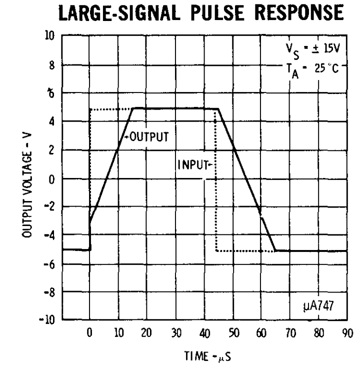
TRANSIENT RESPONSE



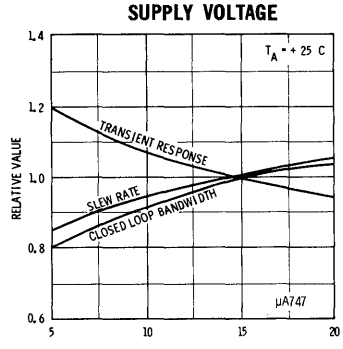
TRANSIENT RESPONSE TEST CIRCUIT



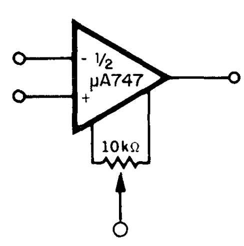
VOLTAGE FOLLOWER LARGE-SIGNAL PULSE RESPONSE



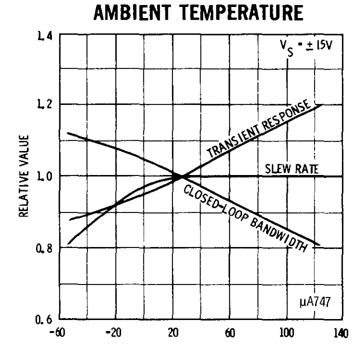
FREQUENCY CHARACTERISTICS AS A FUNCTION OF SUPPLY VOLTAGE



VOLTAGE OFFSET NULL CIRCUIT

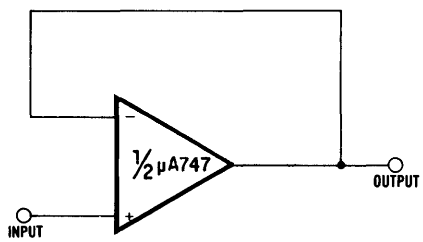


FREQUENCY CHARACTERISTICS AS A FUNCTION OF AMBIENT TEMPERATURE



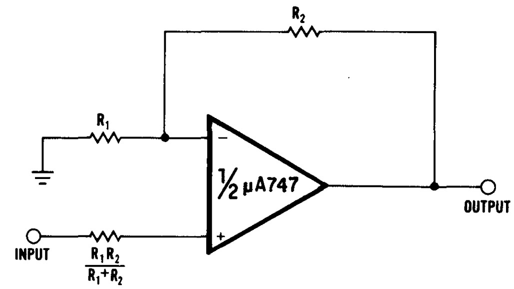
TYPICAL APPLICATIONS

UNITY-GAIN VOLTAGE FOLLOWER



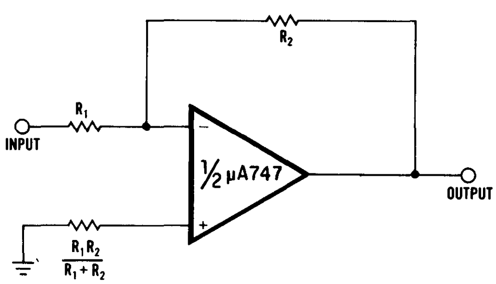
$R_{IN} = 400\ M\Omega$
$C_{IN} = 1\ pF$
$R_{out} << 1\ \Omega$
$B.W. = 1\ MHz$

NON-INVERTING AMPLIFIER



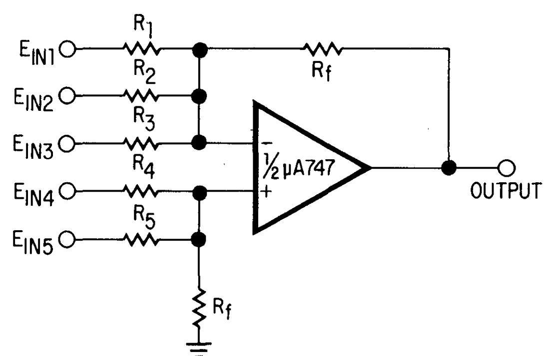
GAIN	R_1	R_2	B.W.	R_{IN}
10	1 kΩ	9 kΩ	100 kHz	400 MΩ
100	100 Ω	9.9 kΩ	10 kHz	280 MΩ
1000	100 Ω	99.9 kΩ	1 kHz	80 MΩ

INVERTING AMPLIFIER



GAIN	R_1	R_2	B.W.	R_{IN}
1	10 kΩ	10 kΩ	1 MHz	10 kΩ
10	1 kΩ	10 kΩ	100 kHz	1 kΩ
100	1 kΩ	100 kΩ	10 kHz	1 kΩ
1000	100 Ω	100 kΩ	1 kHz	100 Ω

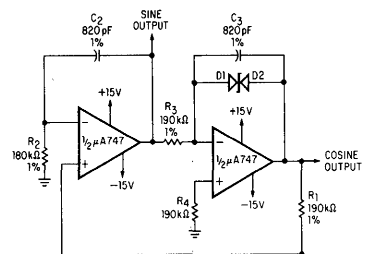
WEIGHTED AVERAGING AMPLIFIER



$$-E_{out} = E_{IN1}\left(\frac{R_f}{R_1}\right) + E_{IN2}\left(\frac{R_f}{R_2}\right) + E_{IN3}\left(\frac{R_f}{R_3}\right) - E_{IN4}\left(\frac{R_f}{R_4}\right) - E_{IN5}\left(\frac{R_f}{R_5}\right)$$

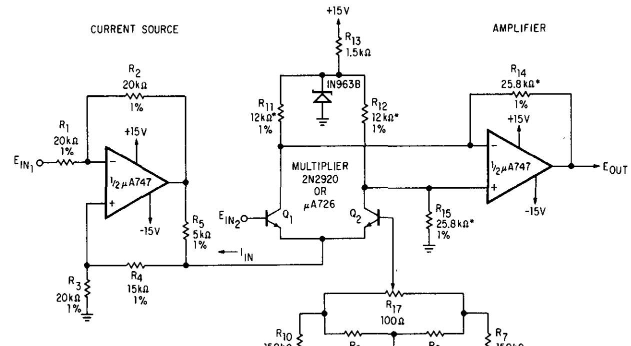
TYPICAL APPLICATIONS

QUADRATURE OSCILLATOR



$f = \frac{1}{2\pi\sqrt{C_2R_2C_3R_3}}$ $(R_1C_1 = R_2C_2)$

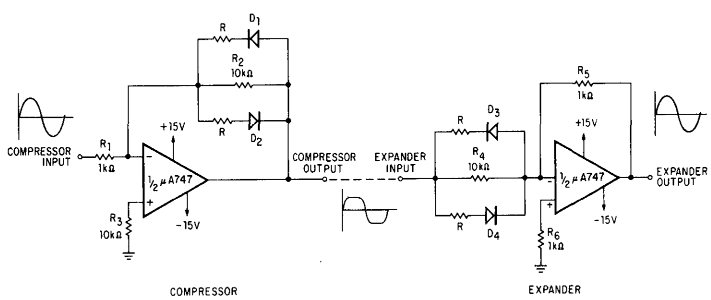
ANALOG MULTIPLIER



*Matched to 0.1%

$E_{OUT} = 100\, E_{IN_1} \times E_{IN_2}$

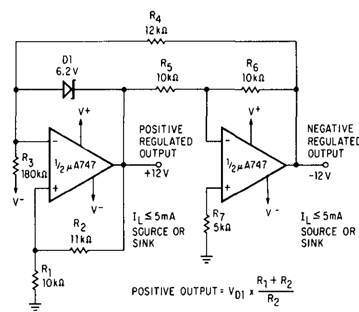
COMPRESSOR/EXPANDER AMPLIFIERS



MAXIMUM COMPRESSION EXPANSION RATIO = R_1/R (10kΩ > R ≥ 0)

NOTE: DIODES D_1 THROUGH D_4 ARE MATCHED FD6666 OR EQUIVALENT

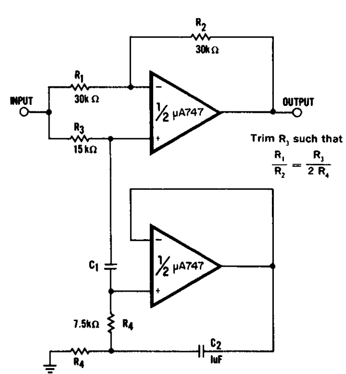
TRACKING POSITIVE AND NEGATIVE VOLTAGE REFERENCES



POSITIVE OUTPUT $= V_{D1} \times \frac{R_1 + R_2}{R_2}$

NEGATIVE OUTPUT $= -$POSITIVE OUTPUT $\times \frac{R_6}{R_5}$

NOTCH FILTER USING THE μA747 AS A GYRATOR



NOTCH FREQUENCY AS A FUNCTION OF C_1